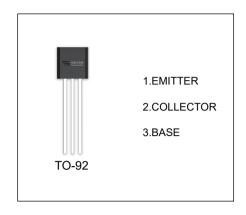


KSC1730 TRANSISTOR (NPN)

FEATURES

- High Transition Frequency
- Low V_{CE(sat)}



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
KSC1730	TO-92	Bulk	1000pcs/Bag
KSC1730-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS (T_a =25 $^{\circ}$ C unless otherwise noted)

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	30	V
V _{CEO}	Collector-Emitter Voltage	15	\
V _{EBO}	Emitter-Base Voltage	5	V
Ic	Collector Current	50	mA
Pc	Collector Power Dissipation	200	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	625	°C/W
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	°C



Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 0.01mA,I _E =0	30			V
Collector-emitter breakdown	$V_{(BR)CEO}$	$I_C=5mA,I_B=0$	15			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =0.01mA,I _C =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} =12V,I _E =0			0.1	μA
DC current gain	h _{FE}	V _{CE} =10V, I _C =5mA	40		240	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =10mA,I _B =1mA			0.5	V
Collector output capacitance	C _{ob}	V _{CB} =10V,I _E =0, f=1MHz			1.5	pF
Transition frequency	f _T	VcE=10V,Ic= 5mA	800			MHz

CLASSIFICATION OF h_{FE}

RANK	R	0	Y
RANGE	40-80	70-140	120-240